## **Vishay Semiconductors**

Hyperfast Rectifier, 3 A FRED Pt®



click logo to get started

DESIGN SUPPORT TOOLS



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	3 A			
V <sub>R</sub>	200 V			
V <sub>F</sub> at I <sub>F</sub>	0.74 V			
t <sub>rr</sub>	30 ns			
T <sub>J</sub> max.	175 °C			
Package	SlimSMA (DO-221AC)			
Circuit configuration	Single			

#### **FEATURES**

• Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery



COMPLIANT HALOGEN

FREE

- 175 °C maximum operating junction temperature
- Specific for output and snubber operation
- Low forward voltage drop
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo-injection, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V <sub>RRM</sub>		200	V		
Average rectified forward current	I <sub>F(AV)</sub>	$T_{\rm C} = 145 \ ^{\circ}{\rm C}^{(1)}$	3	٨		
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	85	A		
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C		

#### Note

<sup>(1)</sup> Device on PCB with 8 mm x 16 mm soldering lands

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25 \ ^{\circ}C$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	200	-	-		
Forward voltage	VF	I <sub>F</sub> = 3 A	-	0.86	0.93	V	
i orward voltage	VF	I <sub>F</sub> = 3 A, T <sub>J</sub> = 125 °C	-	0.74	0.78		
Reverse leakage current	I <sub>R</sub>	$V_{R} = V_{R}$ rated	-	-	2		
		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	1	8	μA	
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	13	-	pF	

kert





www.vishay.com

# Vishay Semiconductors

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, dI_F/dt = 50$	0 Α/μs, V <sub>R</sub> = 30 V	-	26	-		
Reverse recovery time	+	I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1 A, I <sub>rr</sub> = 0.25 A		-	-	30		
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	18	-	ns	
		T <sub>J</sub> = 125 °C		-	26	-		
Deals receiver a current		T <sub>J</sub> = 25 °C	$I_F = 3 A$	-	2.5	-	А	
Peak recovery current I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	dI <sub>F</sub> /dt = 200 A/µs V <sub>B</sub> = 160 V	-	4	-	A		
Reverse recovery charge Q <sub>rr</sub>	0	T <sub>J</sub> = 25 °C		-	23	-	nC	
	Qrr	T <sub>J</sub> = 125 °C		-	50	-	no	

<b>THERMAL - MECHANICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 $^{\circ}$ C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C	
Thermal resistance, junction to lead	R <sub>thJL</sub>	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	8	10	°C/W	
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	91	110	C/W	
Approvimate Waight				0.032		g	
Approximate Weight				0.0011		oz.	
Marking device		Case style SlimSMA (DO-221AC)		31	H2		

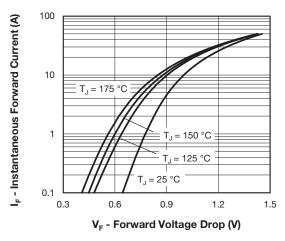


Fig. 1 - Typical Forward Voltage Drop Characteristics

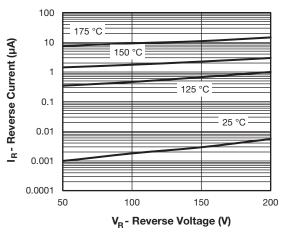


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



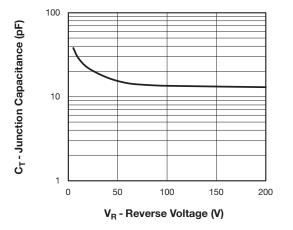


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

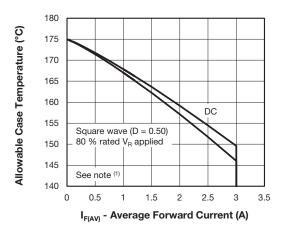


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

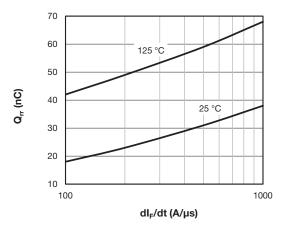


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

Revision: 07-May-2018

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ \mathsf{x} \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{Fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$ 

3.5 **RMS** limit 3 Average Power Loss (W) 2.5 2 D = 0.201.5 D = 0.25D = 0.33 1 D = 0.50 D = 0.75 DC 0.5 0 0 0.6 1.2 1.8 2.4 3 3.6 4.2 4.8

Average Forward Current - I<sub>F(AV)</sub> (A)

Fig. 5 - Forward Power Loss Characteristics

VS-3EJH02HM3

**Vishay Semiconductors** 

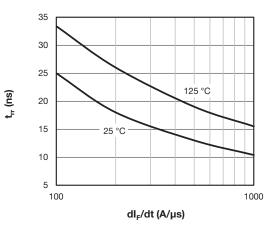
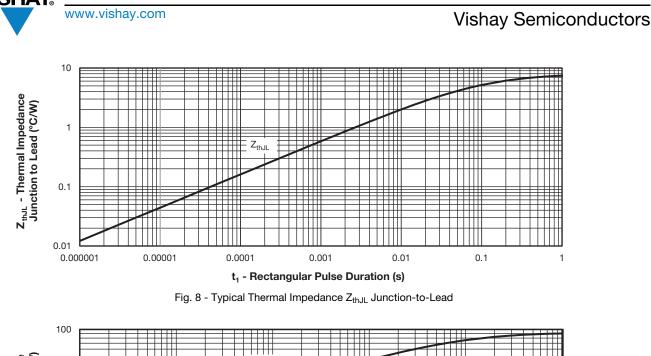


Fig. 6 - Typical Reverse Recovery vs. dl<sub>F</sub>/dt

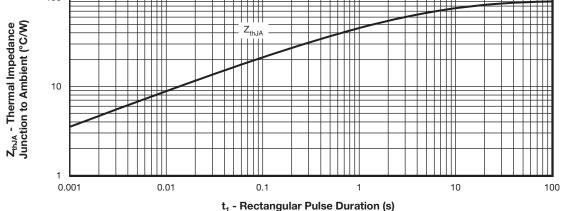
Document Number: 94878

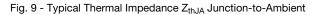
3

For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



VS-3EJH02HM3





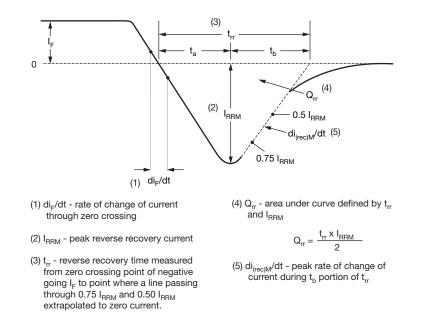


Fig. 10 - Reverse Recovery Waveform and Definitions

Revision: 07-May-2018	4	Document Number: 94878
For technical questions within your region	r: <u>DiodesAmericas@vishay.com</u> , <u>DiodesAsia@vishay.co</u>	m, <u>DiodesEurope@vishay.com</u>
	BE WITHOUT NOTICE. THE PRODUCTS DESCRIBED CIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com</u>	

## Vishay Semiconductors

### **ORDERING INFORMATION TABLE**

www.vishay.com

VISHAY

Device code	VS-	3	Е	J	н	02	н	М3
		2	3	4	5	6	7	8
	1 · 2 · 3 ·	Cur	rent rati	niconduo ng (3 = iguration	3 A)	oduct		
	4 - 5 -	E = J =	single c	liode A packa				
	6 - 7 - 8 -	· Volt · H =	age coo AEC-Q	ast recov de (02 = 101 qua en-free,	200 V) alified	complia	nt, and	termina

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-3EJH02HM3/6A	3500	3500	7"diameter plastic tape and reel				
VS-3EJH02HM3/6B	14 000	14 000	13"diameter plastic tape and reel				

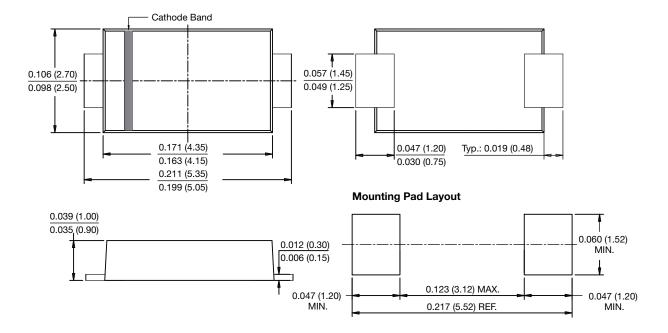
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95571				
Part marking information	www.vishay.com/doc?95562				
Packaging information	www.vishay.com/doc?88869				
SPICE model	www.vishay.com/doc?96050				



**Vishay Semiconductors** 

# DO-221AC (SlimSMA)

### **DIMENSIONS** in inches (millimeters)





Vishay

## Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.